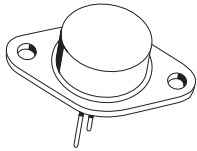


MJ4032 PNP
MJ4035 NPN

**COMPLEMENTARY SILICON
POWER DARLINGTON TRANSISTORS**



TO-3 CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR MJ4032, MJ4035 types are Complementary Silicon Power Darlington Transistors designed for general purpose and amplifier applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

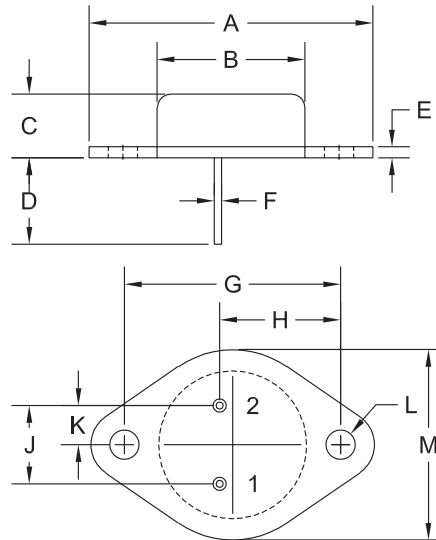
	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	16	A
Base Current	I_B	0.5	A
Power Dissipation	P_D	150	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +200	$^{\circ}\text{C}$
Thermal Resistance	Θ_{JC}	1.17	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CER}	$V_{CE}=100\text{V}, R_{BE}=1.0\text{k}\Omega$		1.0	mA
I_{CER}	$V_{CE}=100\text{V}, R_{BE}=1.0\text{k}\Omega, T_C=150^{\circ}\text{C}$		5.0	mA
I_{CEO}	$V_{CE}=50\text{V}$		3.0	mA
I_{EBO}	$V_{EB}=5.0\text{V}$		5.0	mA
BV_{CEO}	$I_C=100\text{mA}$	100		V
$V_{CE(SAT)}$	$I_C=10\text{A}, I_B=40\text{mA}$		2.5	V
$V_{CE(SAT)}$	$I_C=16\text{A}, I_B=80\text{mA}$		4.0	V
$V_{BE(ON)}$	$V_{CE}=3.0\text{V}, I_C=10\text{A}$		3.0	V
h_{FE}	$V_{CE}=3.0\text{V}, I_C=10\text{A}$	1000		

R0 (4-May 2009)

TO-3 CASE - MECHANICAL OUTLINE



R2

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.516	1.573	38.50	39.96
B (DIA)	0.748	0.875	19.00	22.23
C	0.250	0.450	6.35	11.43
D	0.433	0.516	11.00	13.10
E	0.054	0.065	1.38	1.65
F	0.035	0.045	0.90	1.15
G	1.177	1.197	29.90	30.40
H	0.650	0.681	16.50	17.30
J	0.420	0.440	10.67	11.18
K	0.205	0.225	5.21	5.72
L (DIA)	0.151	0.172	3.84	4.36
M	0.984	1.050	25.00	26.67

TO-3 (REV: R2)

LEAD CODE:

- 1) BASE
- 2) EMITTER
- C) COLLECTOR

MARKING: FULL PART NUMBER

R0 (4-May 2009)